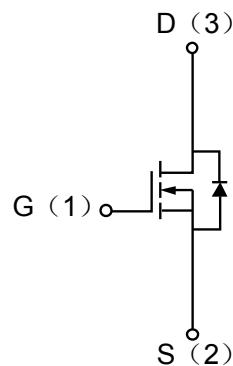


## Description

The MOSFET provide the best combination of fast switching, low on-resistance and cost-effectiveness.

MOSFET Product Summary		
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A)
60	0.096@ V <sub>GS</sub> =4.5V	3



## Electrical characteristics per line@25°C( unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
<b>OFF/ON CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	I <sub>D</sub> = 250µA, V <sub>GS</sub> = 0V	60		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V	-	-	1	µA
		V <sub>DS</sub> = 60V, V <sub>GS</sub> = 0V T <sub>J</sub> = 55°C			10	
Gate-Body Leakage Current	I <sub>GS</sub>	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±20V	-	-	±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA	0.7	-	2.0	V
Static Drain-Source On-Resistance <sup>2</sup>	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 2.1A	-	0.096	0.130	Ω
		V <sub>GS</sub> = 10V, I <sub>D</sub> = 2.6A	-	0.082	0.100	Ω
<b>DYNAMIC PARAMETERS</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 30V, f = 1MHz	-	350		pF
Output Capacitance	C <sub>oss</sub>		-	40		pF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	12		pF
<b>SWITCHING PARAMETERS</b>						
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 10V, R <sub>G</sub> = 1Ω, R <sub>L</sub> = 20Ω I <sub>D</sub> = 1A	-	10		ns
Turn-Off Delay Time	t <sub>d(off)</sub>		-	29		ns
Turn-On Rise Time	t <sub>r</sub>		-	11		ns
Turn-On Fall Time	t <sub>f</sub>		-	3		ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 10V, I <sub>D</sub> = 2.6A		12		nC
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 2.6A		6.5		nC
Gate-Source Charge	Q <sub>gs</sub>			2.2		nC
Gate-Drain Charge	Q <sub>gd</sub>			2.7		nC
Drain-Source Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0V, I <sub>S</sub> = 1.0A		0.8	1.2	V

**Absolute maximum rating@25°C**

Parameter	Symbol	Value	Units
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current ( $T_A=25^\circ\text{C}$ )	$I_D$	3	A
$T_A=70^\circ\text{C}$		2.1	
Pulsed Drain Current	$I_{DM}$	10	A
Maximum Power Dissipation	$P_D$	1.04	W
$T_A=70^\circ\text{C}$		0.67	
Operating Junction and Storage Temperature Range	$T_J$	-55 to 150	°C
Thermal Resistance-Junction to Ambient	$R_{\theta JA}$	100	°C/W

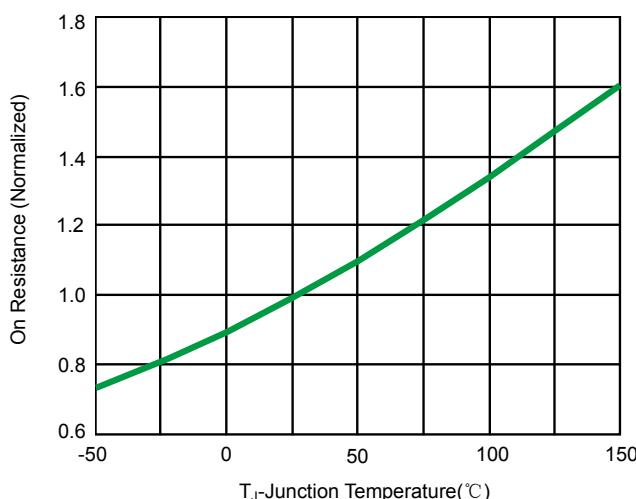
**Typical Characteristics**

Fig 1. On Resistance vs. Junction Temperature

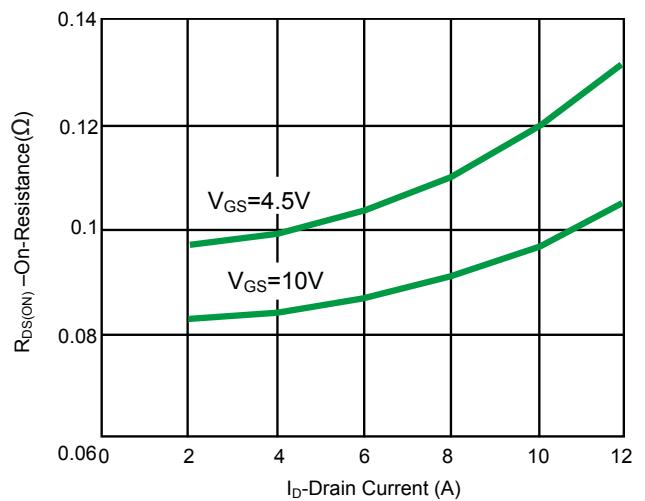


Fig 2. On-Resistance vs. Drain Current

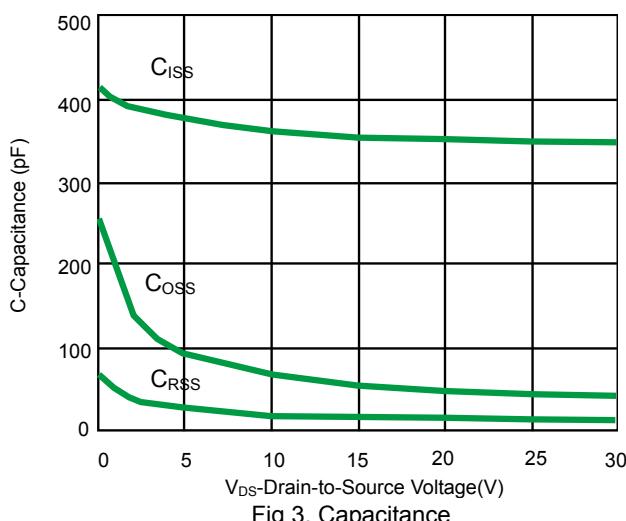


Fig 3. Capacitance

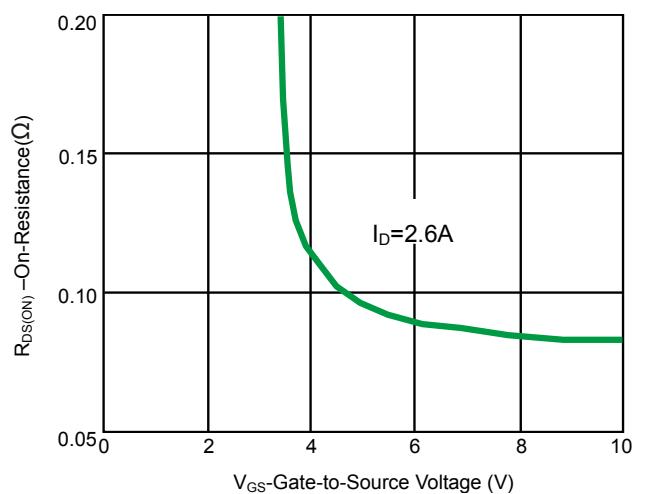


Fig 4. On-Resistance vs. Gate-to-Source Voltage

## N-Channel MOSFET

PNMT60V3

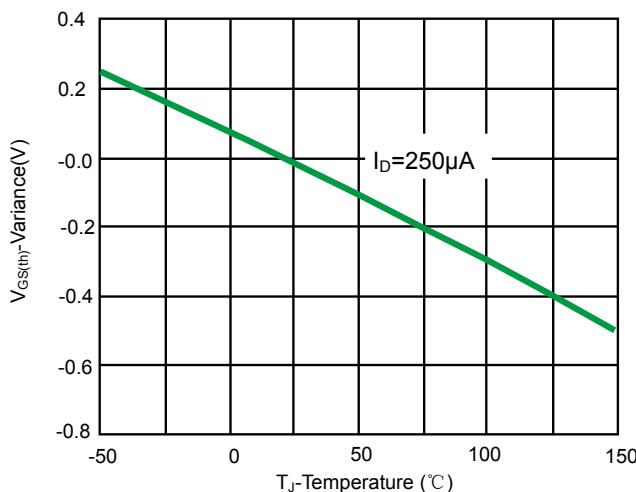


Fig 5. Threshold Voltage

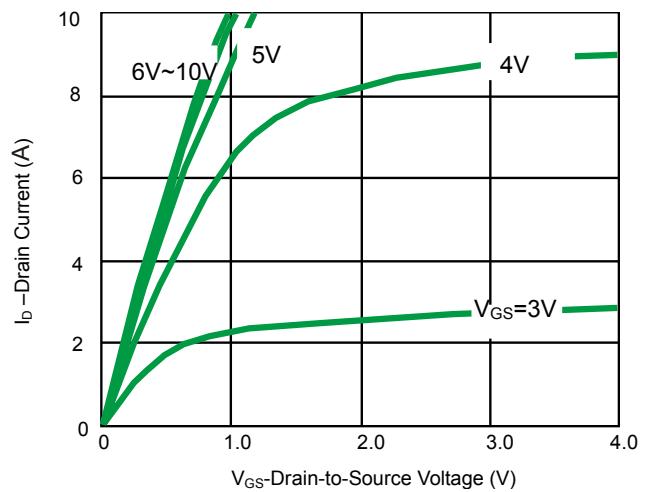


Fig 6. On-Region Characteristics

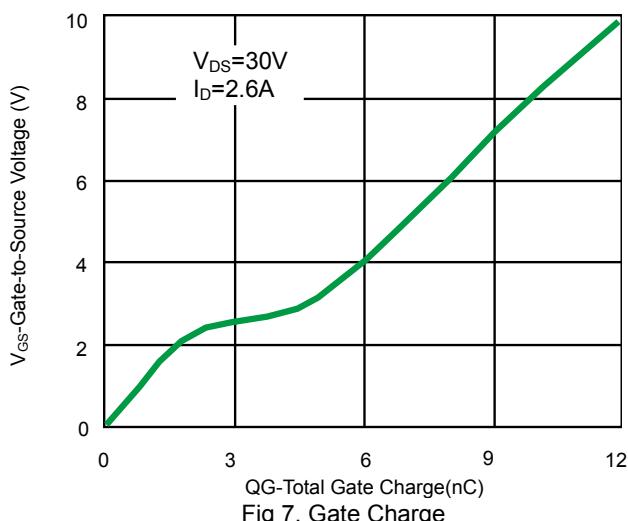


Fig 7. Gate Charge

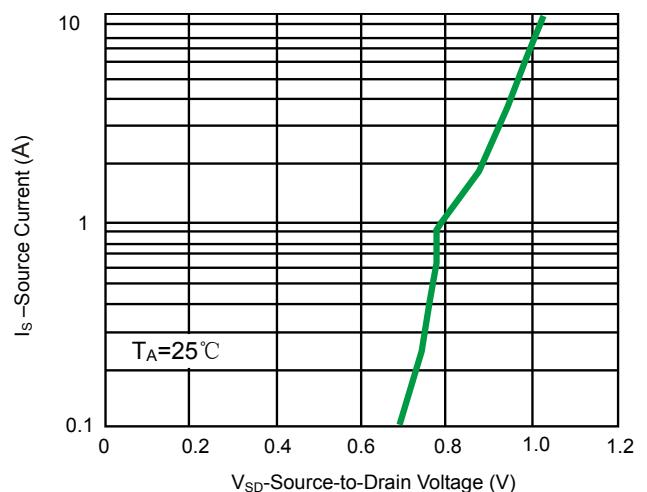


Fig 8. On-Resistance vs. Drain Current

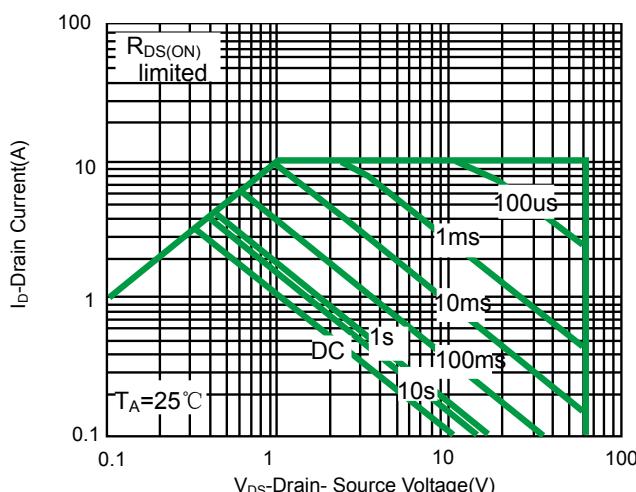


Fig 9. Maximum Forward Biased Safe Operating Area

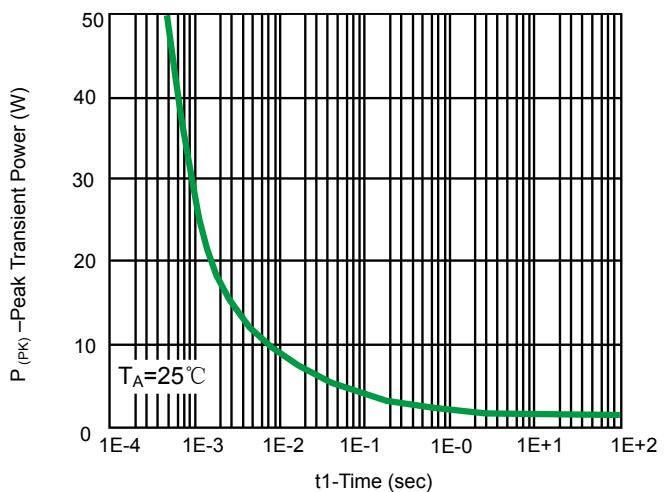


Fig 10. Single Pulse Maximum Power Dissipation

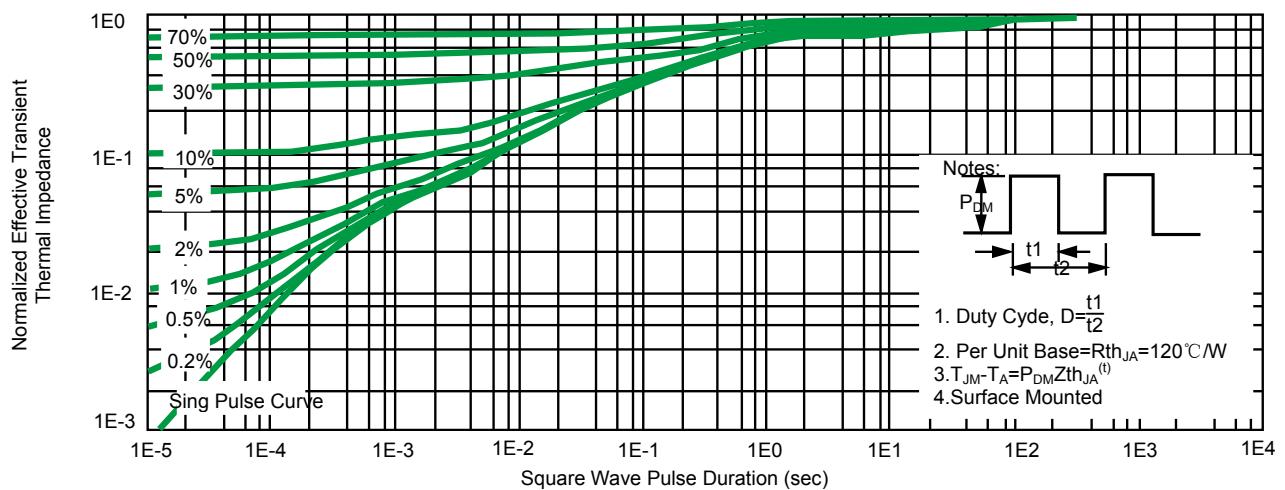
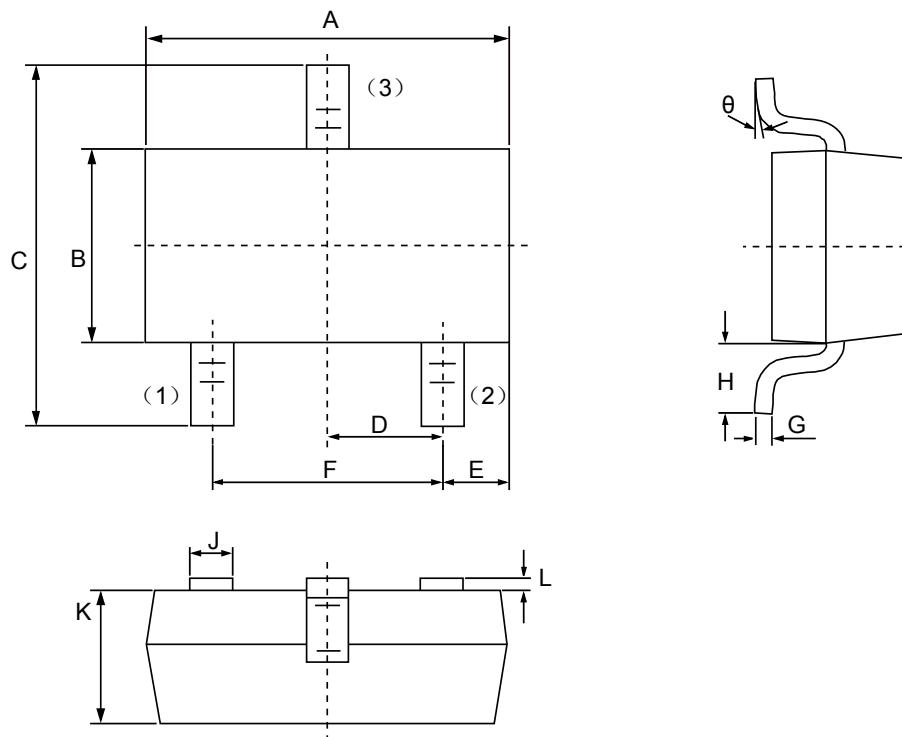


Fig 11. Normalized Thermal Transient Impedance, Junction-to-Ambient

## Product dimension(SOT-23)



Dim	Millimeters		Inches	
	MIN	MAX	MIN	MAX
A	2.80	3.00	0.1102	0.1197
B	1.20	1.40	0.0472	0.0551
C	2.10	2.50	0.0830	0.0984
D	0.89	1.02	0.0350	0.0401
E	0.45	0.60	0.0177	0.0236
F	1.78	2.04	0.0701	0.0807
G	0.085	0.177	0.0034	0.0070
H	0.45	0.60	0.0180	0.0236
J	0.37	0.50	0.0150	0.0200
K	0.89	1.11	0.0350	0.0440
L	0.013	0.100	0.0005	0.0040
θ	0°	10°	0°	10°

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